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November 2013

FDP22N50N

N-Channel UniFETTM II MOSFET 500 V, 22 A, 220 m Ω

Features

- $R_{DS(on)}$ = 185 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 11 A
- Low Gate Charge (Typ. 49 nC)
- Low C_{rss} (Typ. 24 pF)
- · 100% Avalanche Tested
- · Improve dv/dt Capability
- · RoHS Compliant

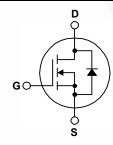
Applications

- PDP TV
- · Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballats





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDP22N50N	Unit
V _{DSS}	Drain to Source Voltage			500	V
V _{GSS}	Gate to Source Voltage			±30	V
	Drain Current	- Continuous (T _C = 25°C)		22	А
ID	DrainCurrent	- Continuous (T _C = 100°C)		13.2	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	88	Α
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	1000	mJ
I _{AR}	Avalanche Current		(Note 1)	22	Α
E _{AR}	Repetitive Avalanche En	ergy	(Note 1)	31.25	mJ
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	10	V/ns
D	Dawer Dissination	(T _C = 25°C)		312.5	W
P_{D}	Power Dissipation	- Derate Above 25°C		2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
TL	Maximum Lead Tempera	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			°C

Thermal Characteristics

Symbol	Parameter	FDP22N50N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	*C/VV

©2009 Fairchild Semiconductor Corporation FDP22N50N Rev. C1

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP22N50N	FDP22N50N	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V,$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.45	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 11 A	-	0.185	0.220	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 11 A	-	24.4	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V		-	2456	3200	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	351	460	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/1/12	-	-\	24	50	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 22 A,		- \	49	65	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	- \	15	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	19	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	22	55	ns
t _r		$V_{DD} = 250 \text{ V}, I_D = 22 \text{ A},$	-	50	110	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 4.7 \Omega$	-	48	110	ns
t _f	Turn-Off Fall Time	(Note 4)	-	35	80	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	88	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 22 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 22 A,	-	472	-	ns
Q_{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	6.5	-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 4.1 mH, I $_{AS}$ = 22 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. I_{SD} \leq 22 A, di/dt \leq 200 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.



Typical Performance Characteristics

Figure 1. On-Region Characteristics

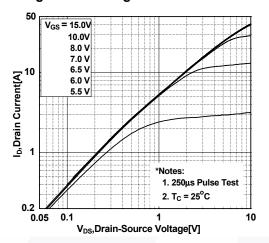


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

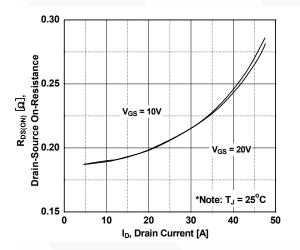


Figure 5. Capacitance Characteristics

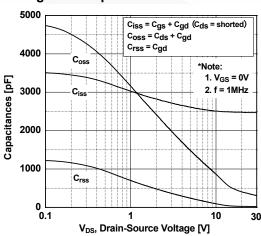


Figure 2. Transfer Characteristics

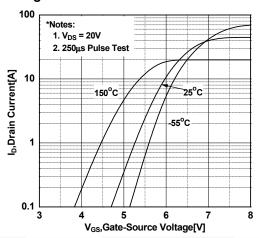


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

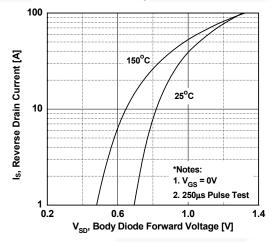
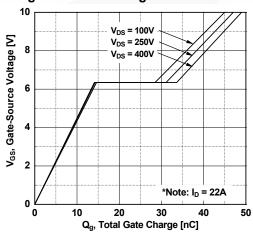


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

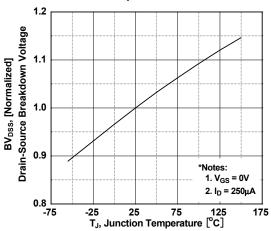


Figure 8. On-Resistance Variation vs. Temperature

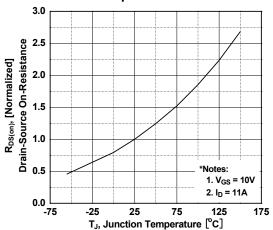


Figure 9. Maximum Safe Operating Area

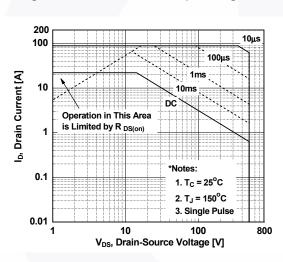


Figure 10. Maximum Drain Current vs. Case Temperature

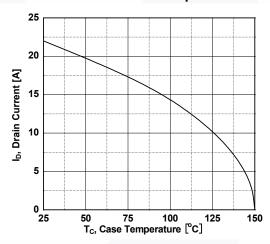
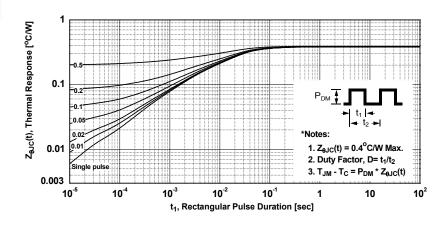


Figure 11. Transient Thermal Response Curve



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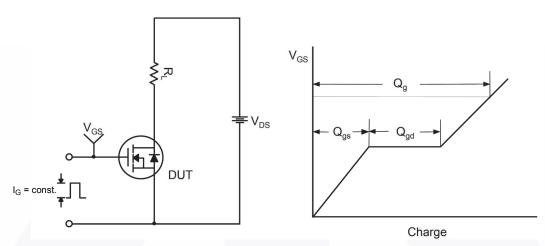


Figure 12. Gate Charge Test Circuit & Waveform

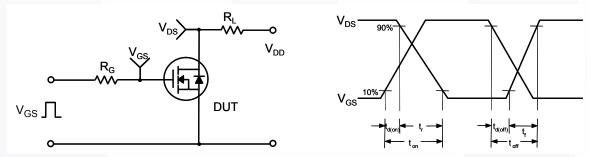


Figure 13. Resistive Switching Test Circuit & Waveforms

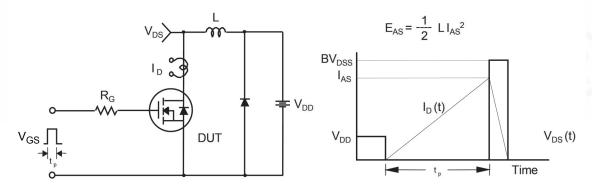


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

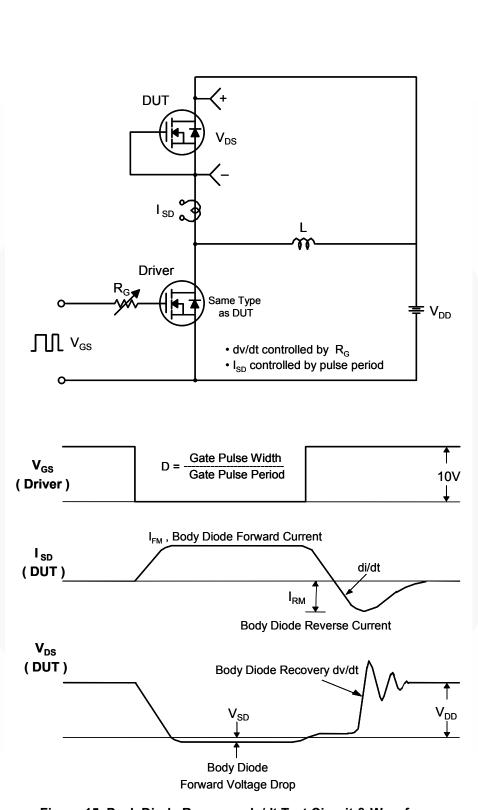


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

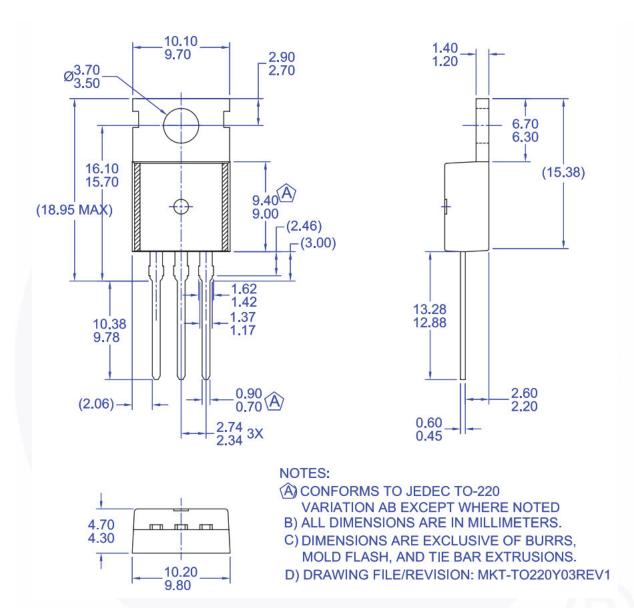


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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